

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) Electronic power device comprising:
 - an active part;
 - a first thin layer made of a semiconductor material and in which the active part is formed;
 - a substrate made of an electrically conductive material;
 - a carrier recombination zone located between the substrate and the first thin layer, wherein the carrier recombination zone provides a resistive electric contact between the substrate and the first thin layer.
2. (Previously Presented) Device as in claim 1, wherein the carrier recombination zone is a second thin layer made of an electrically conductive material and which ensures electrically conductive bonding between the substrate and the first thin layer.
3. (Original) Device as in claim 1, wherein the two sides of the first thin layer are treated to form active zones of the device.
4. (Original) Device as in claim 1, wherein the material in which the carrier recombination zone is made is a metal.

5. (Previously Presented) Device as in claim 1, wherein the material in which the carrier recombination zone is made is an alloy.

6. (Previously Presented) Device as in claim 5, wherein the alloy in which the carrier recombination zone is stable with respect to the materials in which the substrate and the first thin layer are respectively made.

7. (Previously Presented) Device as in claim 1, wherein the material in which the substrate is made is a highly doped semiconductor.

8. (Original) Device as in claim 7, wherein the material in which the carrier recombination zone is made is a metal and this metal is chosen so that, when fabricating the resistive electric contact, it forms a stable alloy with the highly doped semiconductor in which the substrate is made and with the semiconductor material in which the first thin layer is made.

9. (Original) Device as in claim 1, wherein the material in which the substrate is made is a metal.

10. (Original) Device as in claim 9, wherein the carrier recombination zone is made in the metal in which the substrate is made and is formed by part of this substrate.

Claims 11-34 (Cancelled)